ABSTRACT OF THE INVENTION

Etch profile control with pulsed gas flow and its applications to etching such as anisotropic etching of high aspect ratio features and etching of self-aligned contact structures in various processes. Pulsing can be applied according to this invention to the flow rate of a gas such as an etchant gas, a gas that leads to the deposition of a protective layer, a gas that modifies the deposition of a protective layer, and a gas that modifies etching.

G:\DATA\WPDOCS3\JJT\MICRON\185\11675185.PAT

WORKMAN, NYDEGGER & SEELEY A PROFESSIONAL CORPORATION ATTORNEYS AT LAW 1000 EAGLE GATE TOWER 60 EAST SOUTH TEMPLE SALT LAKE CITY, UTAH 84111

The office field of the graph and half first